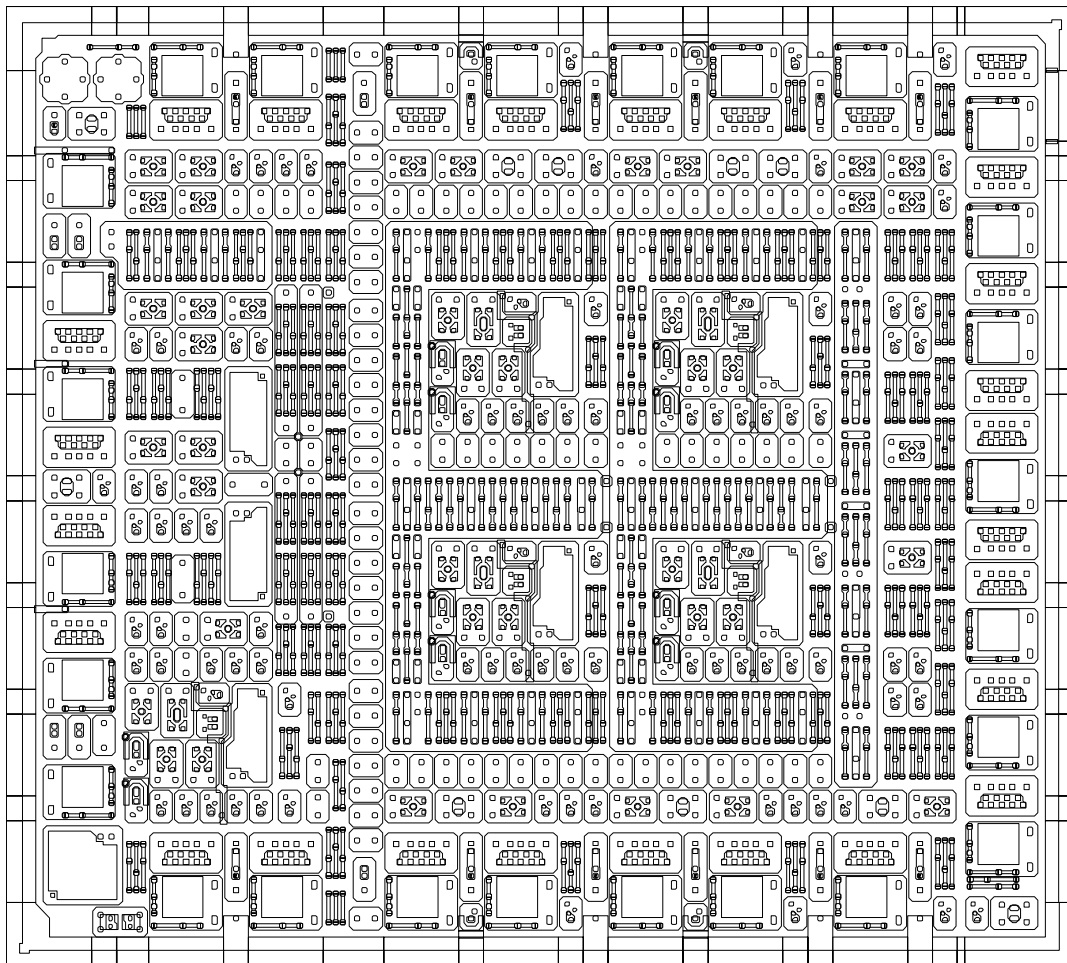


**Special Features:**

- improved  $V_{BE}$ -matching
- Trimmcells
- SiCr Resistors
- Hall Sensor

Die Size	app. 3.3 x 3.0 mm <sup>2</sup>	12 k $\Omega$ Resistor (SiCr)	281
$V_{max}$	36 V	6 k $\Omega$ Resistor (SiCr)	300
Bonding Pads	28	3 k $\Omega$ Resistor (SiCr)	27
50 mA NPN Transistor	27	1.5 k $\Omega$ Resistor (SiCr)	27
10 mA NPN Transistor	10	5 k $\Omega$ Resistor (Epi)	12
5 mA NPN Transistor	99	Crossunder	196
5 mA NPN Transistor (trimmcell)	19	15 pF Capacitor	5
1 mA PNP Transistor lateral	47	17 pF Capacitor	2
2 mA PNP Transistor vertical	19	20 pF Capacitor	1
Hall Sensor vertical	2	Total Resistance (diffused)	182 k $\Omega$
1.2 k $\Omega$ Resistor (base diffused)	102	Total Resistance (SiCr)	5.3 M $\Omega$
0.6 k $\Omega$ Resistor (base diffused)	90	Total Resistance (Epi)	60 k $\Omega$
0.3 k $\Omega$ Resistor (base diffused)	20	Total Capacitance	129 pF



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